High Voltage Transistor

PNP Silicon

Features

• Pb–Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-350	Vdc
Collector-Base Voltage	V _{CBO}	-350	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Base Current	Ι _Β	-250	mA
Collector Current – Continuous	Ι _C	-500	mAdc

THERMAL CHARACTERISTICS

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Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

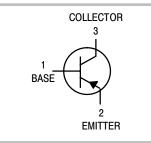
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

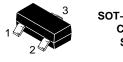
- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



2Z = Device Code

M = Date Code*

= Pb-Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

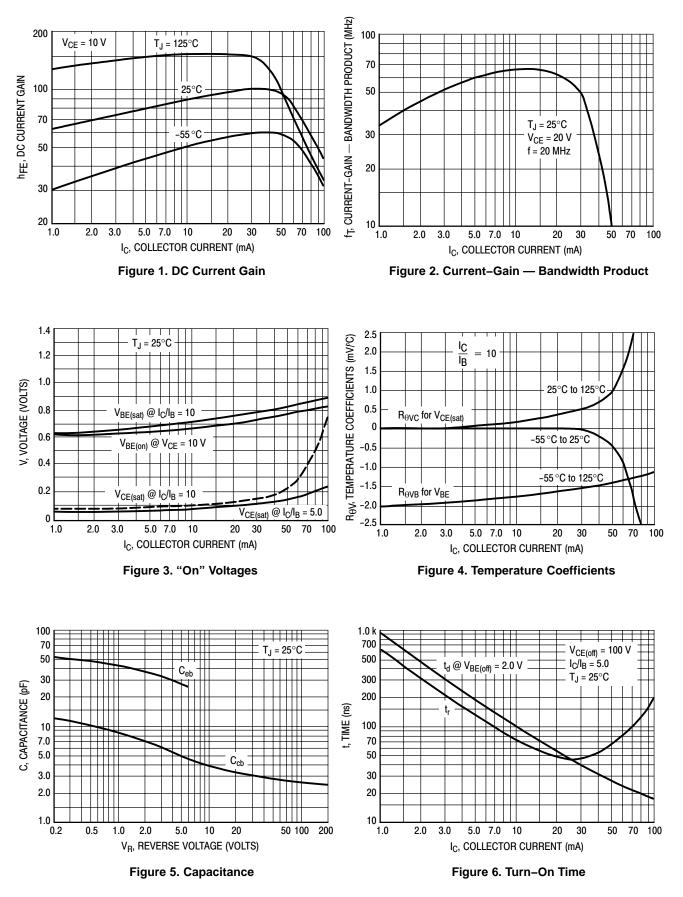
ORDERING INFORMATION

Device	Package	Shipping [†]			
MMBT6520LT1	SOT-23	3,000 / Tape & Reel			
MMBT6520LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel			
MMBT6520LT3	SOT-23	10,000/Tape & Reel			
MMBT6520LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel			

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = $25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage $(I_{C} = -1.0 \text{ mA})$	V _{(BR)CEO}	-350	-	Vdc
Collector–Base Breakdown Voltage $(I_C = -100 \ \mu A)$	V _(BR) CBO	-350	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \ \mu A$)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current ($V_{CB} = -250 \text{ V}$)	I _{CBO}	-	-50	nA
Emitter Cutoff Current (V _{EB} = -4.0 V)	I _{EBO}	-	-50	nA
ON CHARACTERISTICS				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = -1.0 \text{ mA}, \text{ V}_{CE} = -10 \text{ V}) \\ (I_{C} = -10 \text{ mA}, \text{ V}_{CE} = -10 \text{ V}) \\ (I_{C} = -30 \text{ mA}, \text{ V}_{CE} = -10 \text{ V}) \\ (I_{C} = -50 \text{ mA}, \text{ V}_{CE} = -10 \text{ V}) \\ (I_{C} = -100 \text{ mA}, \text{ V}_{CE} = -10 \text{ V}) \end{array} $	h _{FE}	20 30 30 20 15	_ 200 200 _	_
Collector-Emitter Saturation Voltage $(I_C = -10 \text{ mA}, I_B = -1.0 \text{ mA})$ $(I_C = -20 \text{ mA}, I_B = -2.0 \text{ mA})$ $(I_C = -30 \text{ mA}, I_B = -3.0 \text{ mA})$ $(I_C = -50 \text{ mA}, I_B = -5.0 \text{ mA})$	V _{CE(sat)}	- - - -	-0.30 -0.35 -0.50 -1.0	Vdc
$\begin{array}{l} \text{Base-Emitter Saturation Voltage} \\ (I_{C} = -10 \text{ mA}, I_{B} = -1.0 \text{ mA}) \\ (I_{C} = -20 \text{ mA}, I_{B} = -2.0 \text{ mA}) \\ (I_{C} = -30 \text{ mA}, I_{B} = -3.0 \text{ mA}) \end{array}$	V _{BE(sat)}	- - -	-0.75 -0.85 -0.90	Vdc
Base–Emitter On Voltage ($I_C = -100$ mA, $V_{CE} = -10$ V)	V _{BE(on)}	-	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS		1		1
Current–Gain – Bandwidth Product ($I_C = -10 \text{ mA}, V_{CE} = -20 \text{ V}, f = 20 \text{ MHz}$)	f _T	40	200	MHz
Collector–Base Capacitance (V_{CB} = -20 V, f = 1.0 MHz)	C _{cb}	-	6.0	pF
Emitter-Base Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz)	C _{eb}	-	100	pF



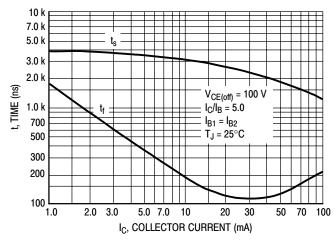
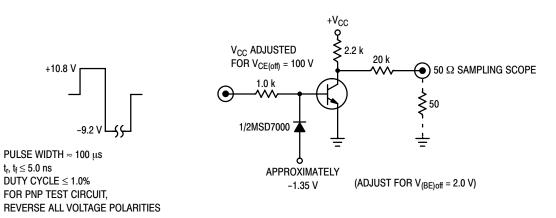
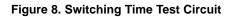


Figure 7. Turn-Off Time





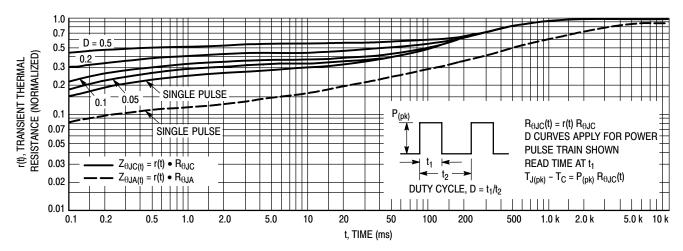
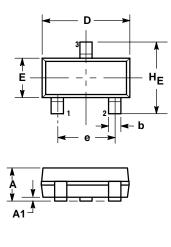
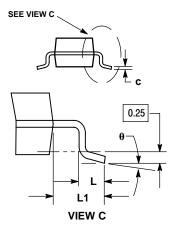


Figure 9. Thermal Response

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD

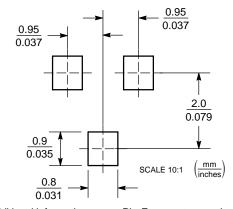
THICKNESS IS THE MINIMUM THICKNESS OF

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2 10	2 40	2 64	0.083	0.094	0 104

STYLE 6:

PIN 1. BASE 2. EMITTER 3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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